



Analog High Speed Optocoupler 1MBd, Photodiode with Transistor Output



## Description

The SDN135 is a high speed optocoupler consisting of an infrared GaAs LED optically coupled through a high isolation barrier to an integrated high speed transistor and photodiode.

Separate access to the photodiode and transistor allow users to reduce base-collector capacitance, enabling much higher switching speeds. Signals with frequencies of up to 2.0MHz can be switched, giving the SDN135 a much broader application range than traditional optocouplers.

The SDN135 comes standard in an 8 pin DIP package.

## Applications

- High Speed Logic Ground Isolation
- Replace Slower Speed Optocouplers
- Line Receivers
- Power Transistor Isolation
- Pulse Transformer Replacement
- Switch Mode Power Supplies
- High Voltage Insulation
- Ground Isolation Analog Signals

## Schematic Diagram



### Features

- TTL Compatible
- High Bit Rate: 1Mb/s
- Bandwidth: 2.0MHz
- Open Collector Output
- High Isolation Voltage (5000V<sub>RMS</sub>)
- High Common Mode Interference Immunity
- RoHS / Pb-Free / REACH Compliant

### Agency Approvals

UL / C-UL:	File # E201932	
VDE:	File # 40035191	(EN 60747-5-2)

## **Absolute Maximum Ratings**

The values indicated are absolute stress ratings. Functional operation of the device is not implied at these or any conditions in excess of those defined in electrical characteristics section of this document. Exposure to absolute Maximum Ratings may cause permanent damage to the device and may adversely affect reliability.

Storage Temperature	55 to +125°C
Operating Temperature	40 to +85°C
Continuous Input Current	40mA
Transient Input Current	400mA
Reverse Input Control Voltage	5V
Input Power Dissipation	40mW
Peak Output Current (Pin 6)	16mA
Max Emitter-Base Reverse Voltage (Pin 5-7)	5V
Max Supply Voltage (Pin 8-5)	15V
Max Output Voltage (Pin 6-5)	15V
Max Base Current (Pin 7)	5mA
Output Power Dissipation	100mW

## **Ordering Information**

Part Number	Description
SDN135	8 pin DIP, (50/Tube)
SDN135-H	0.40" (10.16mm) Lead Spacing (VDE0884)
SDN135-S	8 pin SMD, (50/Tube)
SDN135-STR	8 pin SMD, Tape and Reel (1000/Reel)

NOTE: Suffixes listed above are not included in marking on device for part number identification



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## Electrical Characteristics, T<sub>A</sub> = 25°C (unless otherwise specified)

Parameter	Symbol	Min.	Тур.	Max.	Units	Test Conditions
Input Specifications						
LED Forward Voltage	VF	-	1.4	1.7	V	I <sub>F</sub> = 16mA
LED Reverse Voltage	BV <sub>R</sub>	5	-	-	V	Ι <sub>R</sub> = 10μΑ
Detector Specifications						
Current Transfer Ratio <sup>1</sup>	CTR	7	18	50	%	$I_F = 16 mA, V_{CC} = 4.5 V, V_O = 0.4 V$
Logic Low Output Voltage	V <sub>OL</sub>	-	0.18	0.4	V	$I_F$ =0mA, $V_O$ = $V_{CC}$ =4.5V, $I_O$ =3mA
Logic High Output Current	I <sub>OH</sub>	-	-	0.5	μA	$I_F$ =0mA, $V_O$ = $V_{CC}$ =5.5V
Logic Low Supply Current <sup>2</sup>	I <sub>CCL</sub>	-	400	-	μA	$I_F$ =16mA, $V_O$ =OPEN ( $V_{CC}$ =15V)
Logic High Supply Current <sup>2</sup>	I <sub>CCH</sub>	-	-	1	μA	I <sub>F</sub> =0mA, V <sub>O</sub> =OPEN (V <sub>CC</sub> =15V)
Offset Voltage						
Switching Specifications, T <sub>A</sub> = 0~70°C, V <sub>CC</sub>	= 5V (unless othe	erwise speci	fied)			
Propagation Delay Time to Low Output Level <sup>3</sup>	t <sub>PHL</sub>	-	0.09	1.5	μS	T <sub>A</sub> =25°C (R <sub>L</sub> =4.1KΩ, I <sub>F</sub> =16mA)
Propagation Delay Time to High Output Level <sup>3</sup>	t <sub>PLH</sub>	-	0.8	1.5	μS	T <sub>A</sub> =25°C (R <sub>L</sub> =4.1KΩ, I <sub>F</sub> =16mA)
Logic High Common Mode Transient Immunity <sup>3</sup>	CM <sub>H</sub>	1	-	-	KV/ μS	$I_{F}\text{=}0\text{mA}, V_{CM}\text{=}10V_{P\text{-}P}, R_{L}\text{=}4.1\text{K}\Omega$
Logic High Common Mode Transient Immunity <sup>3</sup>	CM <sub>L</sub>	1	-	-	KV/ μS	$I_{\text{F}}\text{=}16\text{mA}, \text{V}_{\text{CM}}\text{=}10\text{V}_{\text{P-P}}, \text{R}_{\text{L}}\text{=}4.1\text{K}\Omega$
Coupled Capacitance					μS	
Contact Transient Ratio					μS	
Isolation Specifications						
Input-Output Insulation Leakage Current	I <sub>I-O</sub>	-	-	1.0	μA	45% RH, t=5s, V <sub>⊦0</sub> =3kV
Withstand Insulation Test Voltage	V <sub>ISO</sub>	5000	-	-	V <sub>RMS</sub>	RH ≤ 50%, t=1min
Input-Output Resistance	R <sub>I-O</sub>	-	10 <sup>12</sup>	-	Ω	V <sub>I-0</sub> = 500V <sub>DC</sub>

### Notes

1. Current Transfer Ratio (CTR) as a percentage is defined as the ratio of output collector current ( $I_0$ ) to the forward LED input current ( $I_F$ ) times 100

2. A  $0.1 \mu F$  or bigger bypass capacitor for  $V_{\text{CC}}$  is needed as shown in Figure 1 on following page

3. The 4.1K load represents 1LSTTL unit load of 0.36mA and the 6.1K pull-up resistor.



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## **SDN135 Electrical Test Circuits**



Figure 1: Single Channel Test Circuit for t<sub>PHL</sub> and t<sub>PLH</sub>



Figure 2: Single Channel Test Circuit for Common Mode Transient Immunity

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1.4

10

20

28 32 36

24

13

16

19

1.5

1.6

1.7

## SDN135 Performance & Characteristics Plots, T<sub>A</sub> = 25°C, V<sub>cc</sub>=5V (unless otherwise specified)

SOLID STATE



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## SDN135 Solder Reflow Temperature Profile Recommendations

### (1) Infrared Reflow:

Refer to the following figure as an example of an optimal temperature profile for single occurrence infrared reflow. Soldering process should not exceed temperature or time limits expressed herein. Surface temperature of device package should not exceed 250°C:



#### Figure 11

Process Step	Description	Parameter
Α	Preheat Start Temperature (°C)	150°C
В	Preheat Finish Temperature (°C)	180°C
С	Preheat Time (s)	90 - 120s
D	Melting Temperature (°C)	230°C
E	Time above Melting Temperature (s)	30s
F	Peak Temperature, at Terminal (°C)	260°C
G	Dwell Time at Peak Temperature (s)	10s
Н	Cool-down (°C/s)	<6°C/s

### (2) Wave Solder:

Maximum Temperature:	260°C (at terminal)
Maximum Time:	10s
Pre-heating:	100 - 150°C (30 - 90s)
Single Occurrence	

(3) Hand Solder:

Maximum Temperature:	350°C	(at tip of soldering iron)
Maximum Time:	3s	
Single Occurrence		



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## SDN135 Package Dimensions

8 PIN DIP Package







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## SDN135 Package Dimensions

8 PIN WIDE Lead Space Package (-H)









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## SDN135 Package Dimensions

8 PIN SMD Surface Mount Package (-S)









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## SDN135 Packaging Specifications

## Tape & Reel Specifications (T&R)



Specification	Symbol	Dimensions, mm ( inches )
Tape Width	W	$16 \pm 0.3$ ( $0.63$ )
Sprocket Hole Pitch	P0	4 ± 0.1 ( 0.15 )
Compartment Location	F P2	7.5 ± 0.1 ( 0.295 ) 2 ± 0.1 ( 0.079 )
Compartment Pitch	P1	$12 \pm 0.1$ ( $0.472$ )



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